## **Thermal Transport Properties of TlInTe<sub>2</sub> Single Crystals**

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Abstract. Thallium indium ditelluride single crystal, was prepared by a special design constructed by our group. A brass working chamber designed for measuring (TEP) in a wide range of temperature was used. The experimental results indicates that T1InTe<sub>2</sub> is of p-type conductivity. The mobility of charge carriers, holes and electrons was found to be  $2.129 \times 10^3$  cm<sup>2</sup> / V, sec and  $1.218 \times 10^5$  cm<sup>2</sup> / V, sec respectively. The effective masses of the majority and minority carriers were deduced to be  $5.367 \times 10^{-37}$  kg and  $6.856 \times 10^{-43}$  kg respectively. The diffusion coefficient, relaxation time and diffusion length for holes was calculated to be 551.436 cm<sup>2</sup> / sec,  $7.142 \times 10^{-21}$  sec and  $1.986 \times 10^{-9}$  cm respectively. Also  $D_n \cdot \tau_n$ ,  $L_n$  for the electrons was calculated to be  $3.156 \times 10^3$  cm<sup>3</sup> / sec,  $5.222 \times 10^{-26}$  sec and  $1.284 \times 10^{-11}$  cm respectively. In addition to these pronounced parameters, the efficiency of the thermoelectric element (figure of merit) was evaluated, which leads to better application in many fields .

*Keywords: TlInTe*<sub>2</sub>, single crystals, thermoelectric power, semiconductor, charge carriers.